

Features

- Uses PingWei advanced PerfectMOS2 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Excellent Low Ciss
- Qualified according to AEC-Q101 criteria

Benefits

- High robustness and reliability
- Increases maximum current capability
- Low power loss, high power density
- Easy paralleling

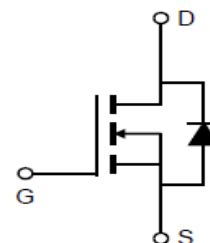
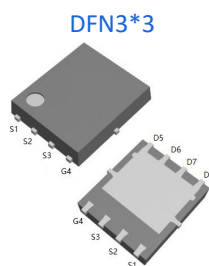
**Applications**

- General Automotive Applications
- Synchronous Rectification for AC/DC Quick Charger
- Battery management
- UPS (Uninterruptible Power Supplies)

100% DVDS Tested
100% Avalanche Tested

Product Summary

V_{DS}	40V
$R_{DS(on)}@10V$ typ	2.9mΩ
I_D (Silicon limit)	95A

**Package Marking and Ordering Information**

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PWC035N04HSQ	C035N04HSQ	DFN3*3	Tape&Reel	13 inches	12mm	5000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	40	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	95 40 67	A
Pulsed drain current ($T_C = 25^\circ\text{C}, t_p=100\mu\text{s}$)	$I_{D \text{ pulse}}$	295	A
Avalanche energy, single pulse ($L=0.1\text{mH}$)	E_{AS}	97	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation $T_C = 25^\circ\text{C}$	P_{tot}	58	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	$^\circ\text{C}$
Reflow soldering temperature (10s)	T_{sold}	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	-	2.6	°C/W	-
Thermal resistance, junction - ambient	RthJA	-	-	90	°C/W	min. footprint

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	40	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	2	-	4	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	-	1 100	μA	V _{DS} =40V, V _{GS} =0V T _j =25°C T _j =150°C
Gate-source leakage current	I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	2.9	3.5	mΩ	V _{GS} =10V, I _D =30A
Transconductance	g _{fs}	-	80	-	S	V _{DS} =5V, I _D =30A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	1935	2903	pF	V _{GS} =0V, V _{DS} =20V, f=100KHz ¹⁾
Output Capacitance	C _{oss}	-	636	953		
Reverse Transfer Capacitance	C _{rss}	-	18	45		
Gate Total Charge	Q _G	-	27	54	nC	V _{DS} =20V, I _D =30A V _{GS} =10V
Gate-Source charge	Q _{GS}	-	11	25		
Gate-Drain charge	Q _{GD}	-	3	10		
Turn-on delay time	t _{d(on)}	-	19	-	ns	V _{GS} =10V, V _{DD} =20V, R _{G_ext} =1.6Ω, I _D =30A
Rise time	t _r	-	53	-		
Turn-off delay time	t _{d(off)}	-	62	-		
Fall time	t _f	-	32	-		
Gate resistance	R _G	-	1.7	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	-	1.2	V	$V_{GS}=0V, I_{SD}=30A$
Body Diode Continuous Forward Current	I_S	-	-	40	A	TC = 25°C
Body Diode Pulsed Current	I_S pulse	-	-	295	A	TC = 25°C, $t_p=100\mu s$

Typical Performance Characteristics

Fig 1: Output Characteristics

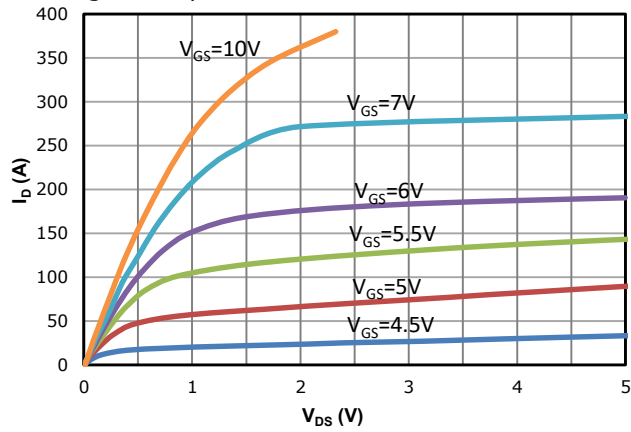


Fig 2: Transfer Characteristics

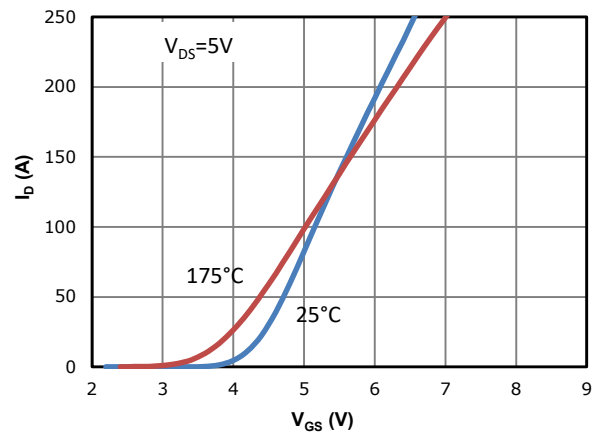


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

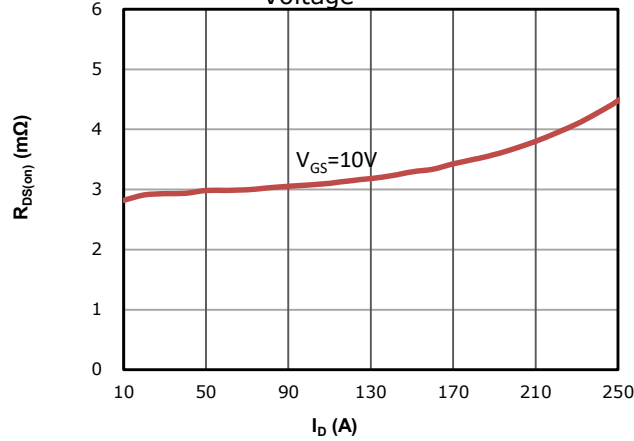


Fig 4: $R_{DS(on)}$ vs Gate Voltage

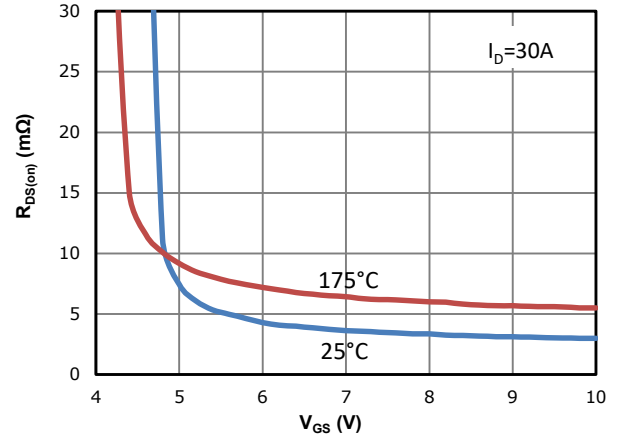


Fig 5: $R_{DS(on)}$ vs. Temperature

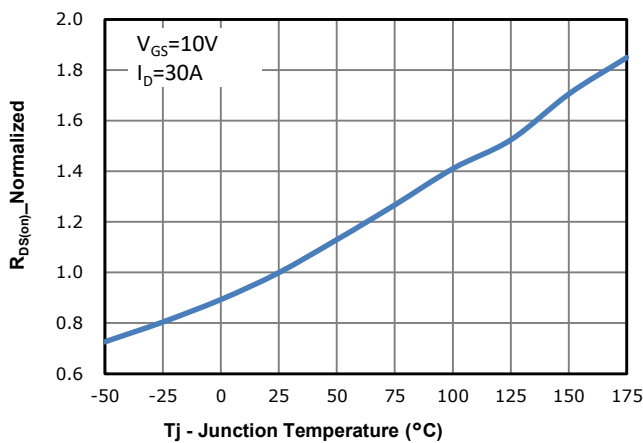


Fig 6: $V_{GS(th)}$ vs. Temperature

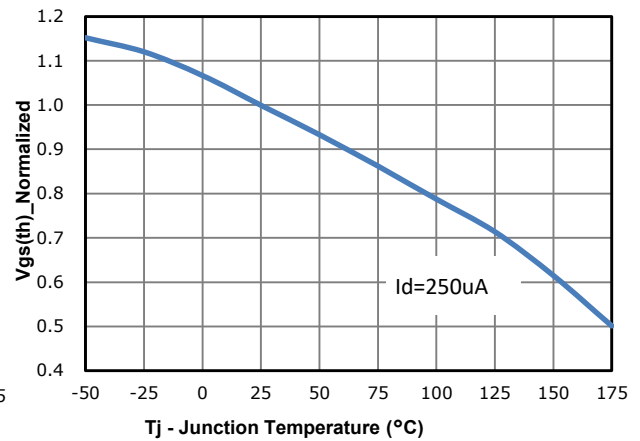


Fig 7: BVdss vs. Temperature

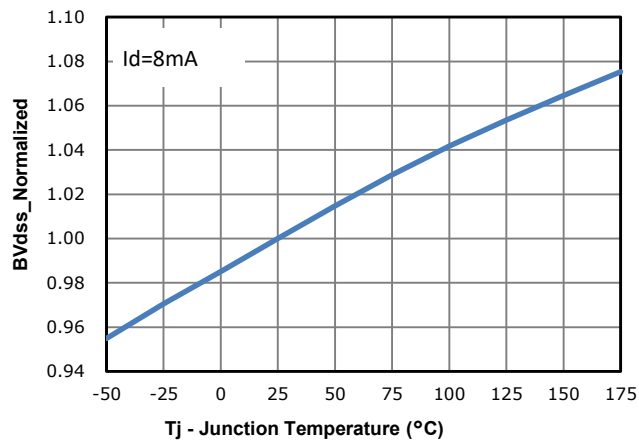


Fig 8: Capacitance Characteristics

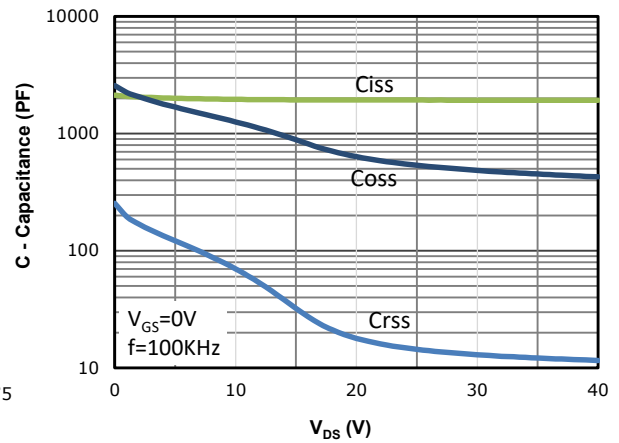


Fig 9: Gate Charge Characteristics

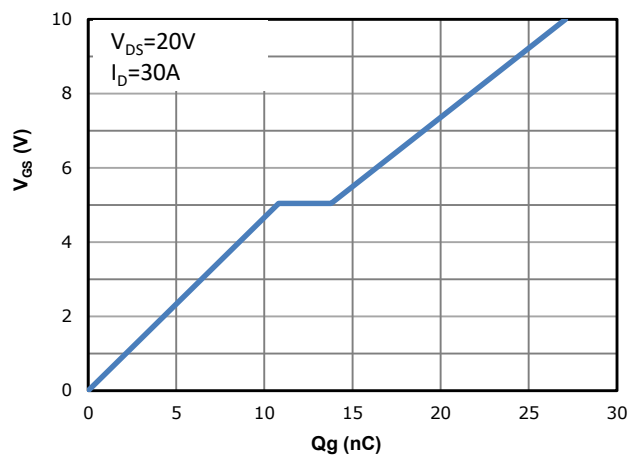


Fig 10: Body-diode Forward Characteristics

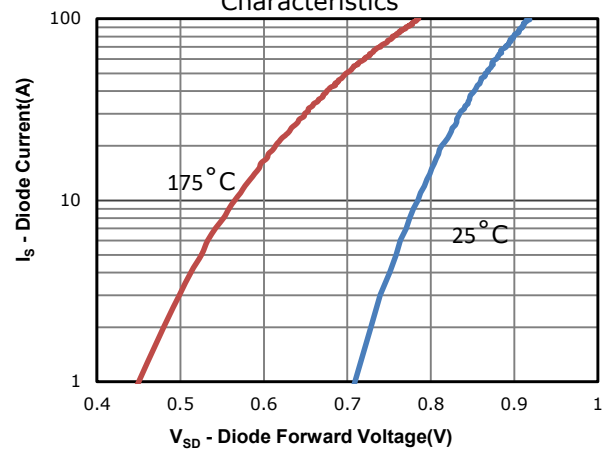


Fig 11: Power Dissipation

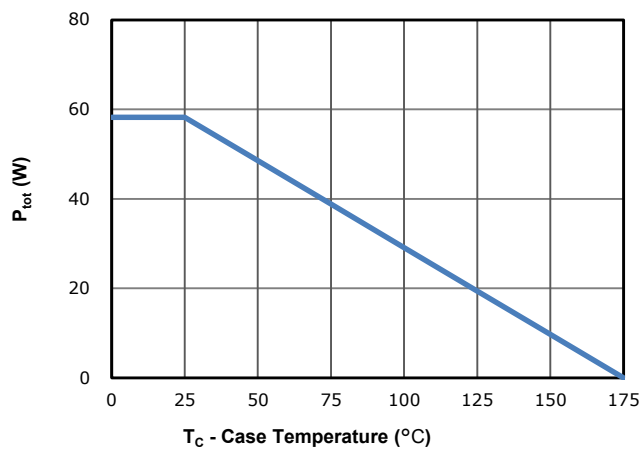


Fig 12: Drain Current Derating

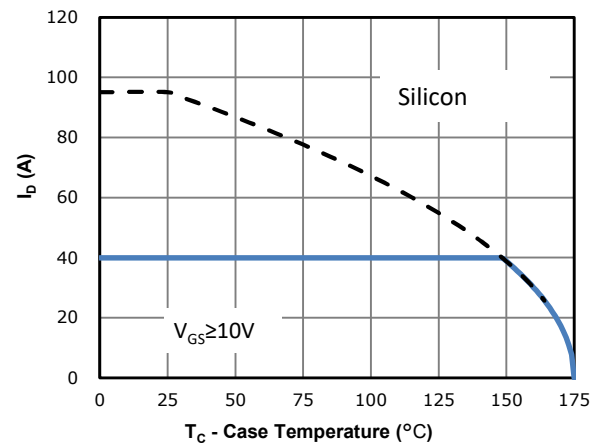


Fig 13: Safe Operating Area

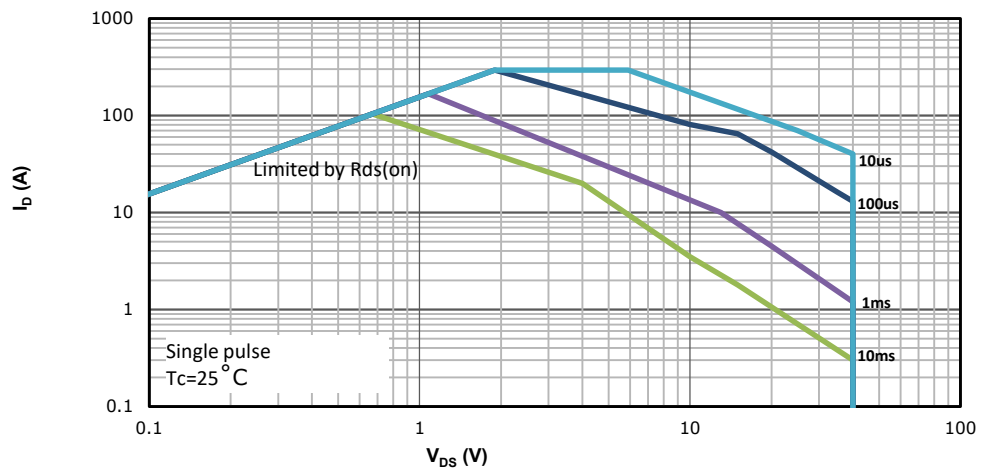
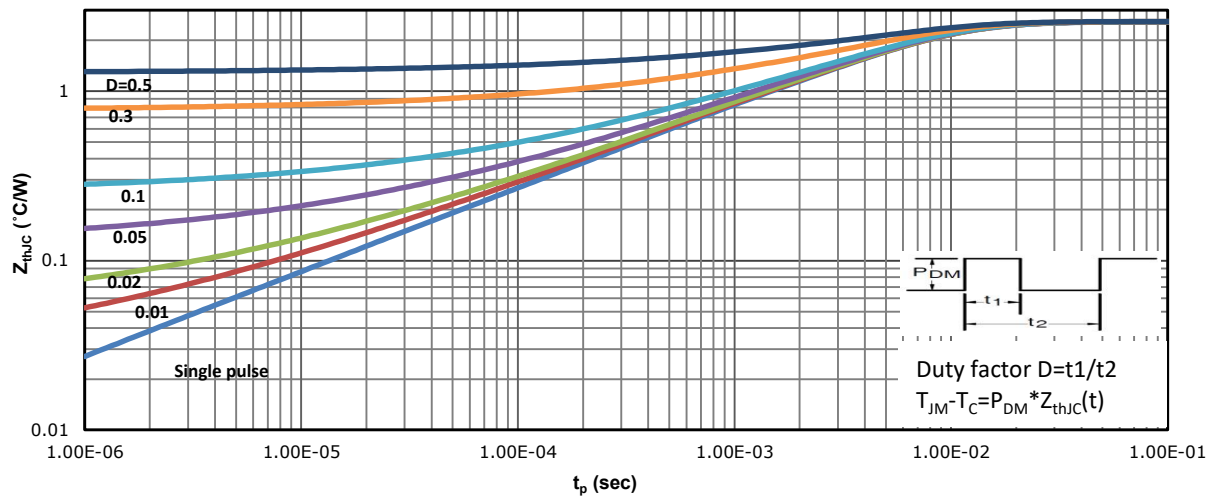
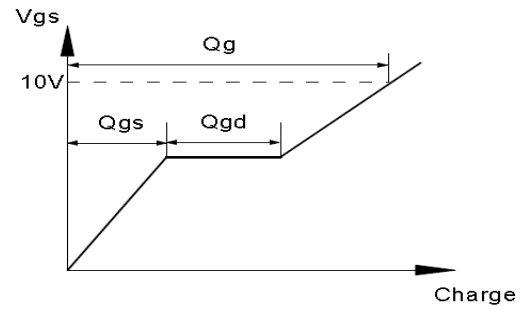


Fig 14: Max. Transient Thermal Impedance

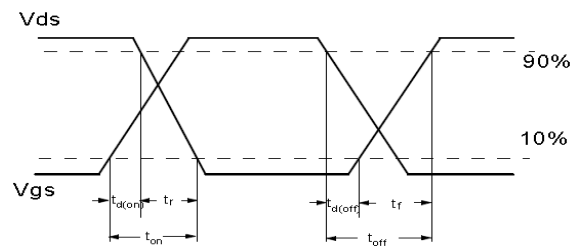


Test Circuit & Waveform

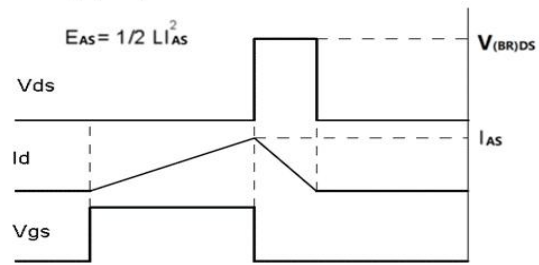
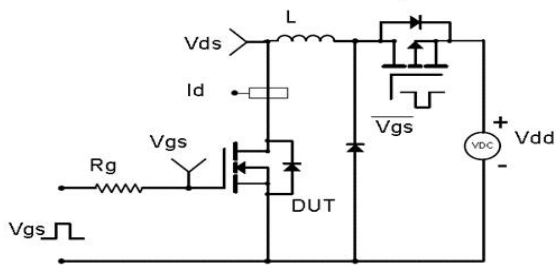
Gate Charge Test Circuit & Waveform



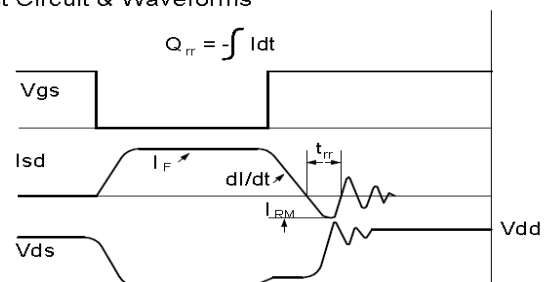
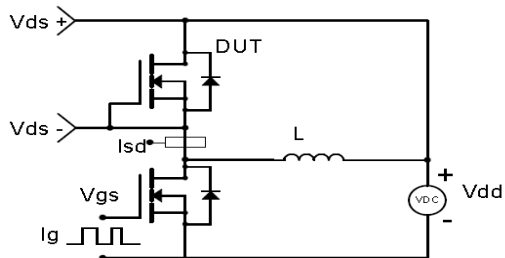
Resistive Switching Test Circuit & Waveforms



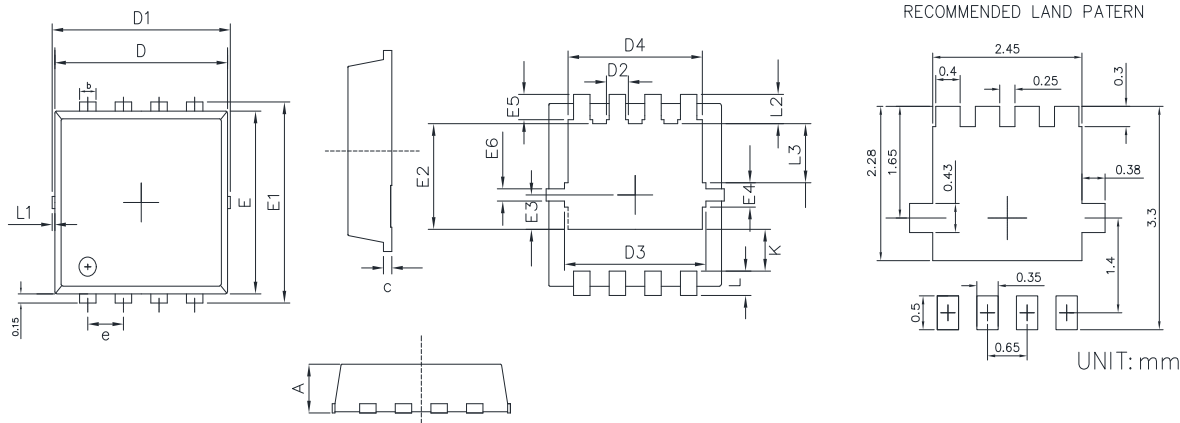
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: DFN3X3



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	1.00	0.028	0.039
b	0.24	0.40	0.009	0.016
c	0.10	0.25	0.004	0.010
D	3.00	3.25	0.118	0.128
D1	3.10	3.50	0.122	0.138
D2	0.30	0.50	0.012	0.020
D3	2.50	2.70	0.098	0.106
D4	2.35	2.55	0.093	0.100
E	2.90	3.10	0.114	0.122
E1	3.15	3.45	0.124	0.136
E2	1.65	1.85	0.065	0.073
E3	0.48	0.68	0.019	0.027
E4	0.23	0.50	0.009	0.020
E5	0.20	0.40	0.008	0.016
E6	0.08	0.25	0.003	0.010
e	0.55	0.75	0.022	0.030
K	0.52	0.82	0.020	0.032
L	0.25	0.55	0.010	0.022
L1	0.00	0.10	0.000	0.004
L2	0.28	0.58	0.011	0.023
L3	0.88	1.08	0.035	0.043

Revision History

Revision	Date	Major changes
1.1	2025/7/21	Add Id(silicon),update Fig12
1.2	2025/11/7	Update Zth,Rjc,Id(pulse),SOA;

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

The product is not intended for use in applications that require extraordinary levels of quality and reliability, such as aviation/aerospace and life-support devices or systems.

Buyer is responsible for its products and applications using PingWei products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by PingWei.

"Typical" parameters which may be provided in PingWei data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts

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